TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SC5465

Industrial Applications

Switching Regulator and High Voltage Switching Applications

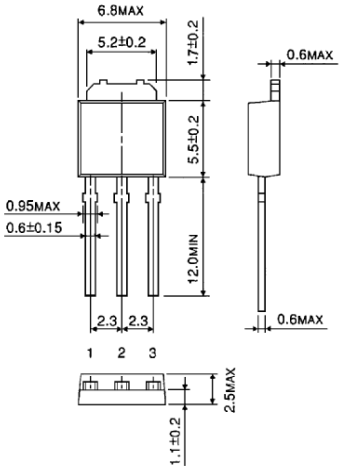
High Speed DC-DC Converter Applications

- Excellent switching times: t_r = 0.7 μs (max)
  t_f = 0.5 μs (max) (I_C = 0.08 A)
- High collector breakdown voltage: V_{CEO} = 800 V

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	900	V
Collector-emitter voltage		V_{CEO}	800	V
Emitter-base voltage		V_{EBO}	7	V
Collector current	DC	I_C	0.8	A
	Pulse	I_{CP}	1.5	
Base current		I_B	0.2	A
Collector power dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		20	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

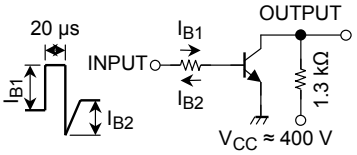
Unit: mm



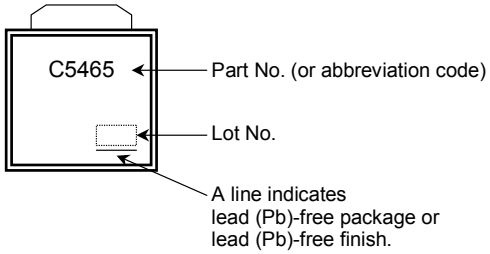
JEDEC	—
JEITA	—
TOSHIBA	2-7B1A

Weight: 0.36 g (typ.)

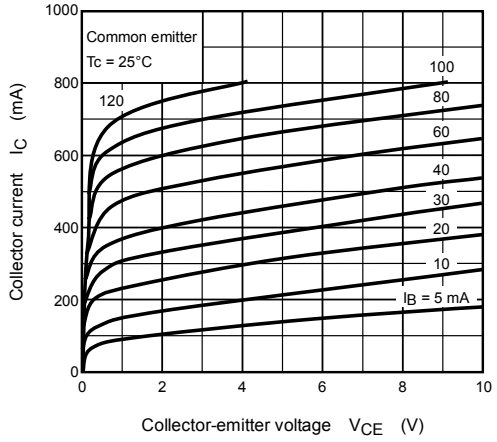
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = 800 V, I_E = 0	—	—	100	μA
Emitter cut-off current		I_{EBO}	V_{EB} = 7 V, I_C = 0	—	—	1	mA
Collector-base breakdown voltage		$V_{(BR)\ CBO}$	I_C = 1 mA, I_E = 0	900	—	—	V
Collector-emitter breakdown voltage		$V_{(BR)\ CEO}$	I_C = 10 mA, I_B = 0	800	—	—	V
DC current gain		$h_{FE\ (1)}$	V_{CE} = 5 V, I_C = 1 mA	10	—	—	
		$h_{FE\ (2)}$	V_{CE} = 5 V, I_C = 0.08 A	15	—	—	
Collector emitter saturation voltage		$V_{CE\ (sat)}$	I_C = 0.3 A, I_B = 0.06 A	—	—	1.0	V
Base-emitter saturation voltage		$V_{BE\ (sat)}$	I_C = 0.3 A, I_B = 0.06 A	—	—	1.3	V
Switching time	Rise time	t_r		—	—	0.7	μs
	Storage time	t_{stg}		—	—	3.0	
	Fall time	t_f	I_{B1} = 0.06 A, I_{B2} = −0.12 A, DUTY CYCLE ≤ 1%	—	—	0.5	

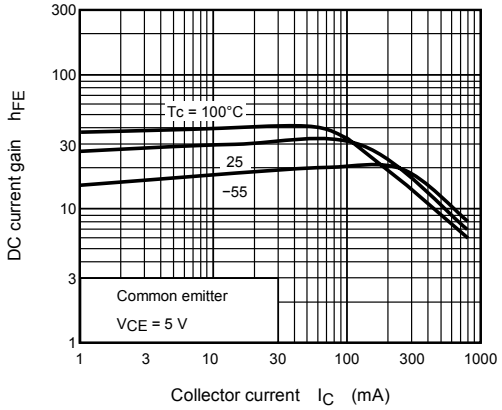
Marking



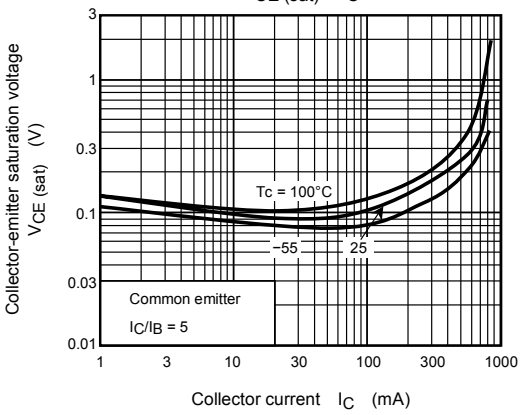
$I_C - V_{CE}$



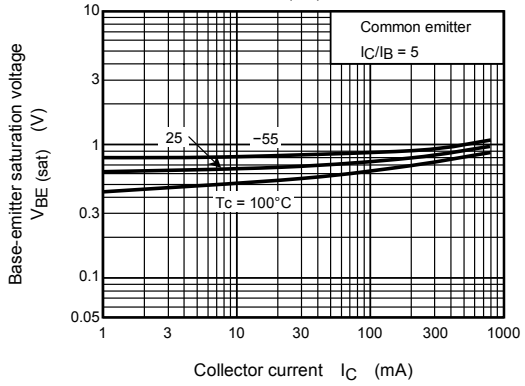
$h_{FE} - I_C$



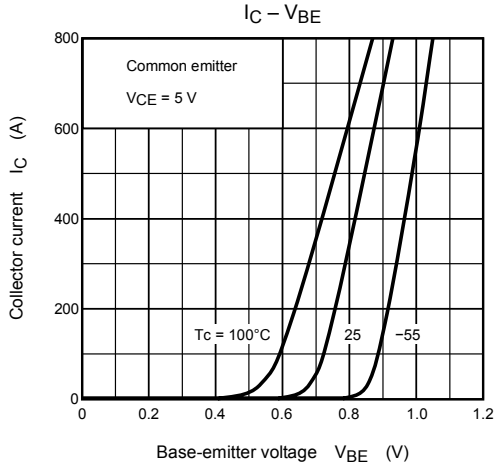
$V_{CE\ (sat)} - I_C$



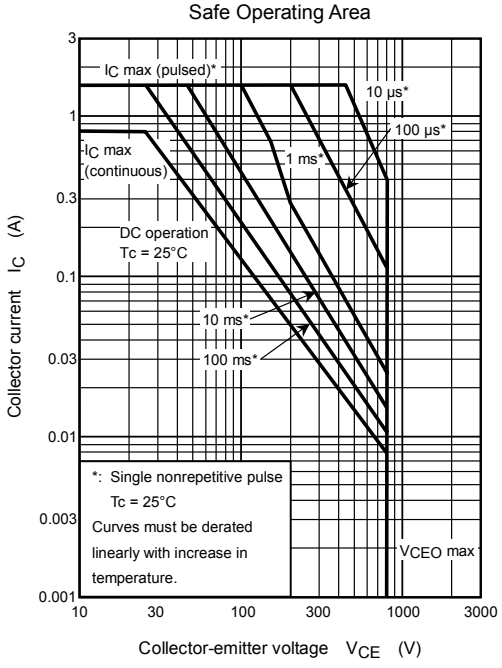
$V_{BE\ (sat)} - I_C$



$I_C - V_{BE}$



Safe Operating Area



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